

In the Specification:

Please make the following changes in the paragraphs at the indicated locations in the originally filed specification:

Page 14, lines 16 to 21:

The entire method with a definite after-heating process, which is conducted either within the growing apparatus in after-heating zone 9 or according to choice in a subsequent tempering process outside of the crystal growing apparatus, leads surprisingly to single crystals with smaller stresses than those of the prior art. The low-stress or stress-poor single crystals according to the invention are outstandingly suitable as the above-described substrates.